

## 1. General description

Hyperfast power diode in a ITO220-2L plastic package



## 2. Features and benefits

- Soft reverse recovery
- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by Epoxy Mold Compound

## 3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Power Factor Correction (PFC)

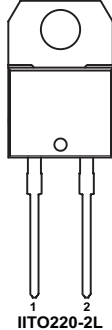
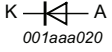
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V <sub>RRM</sub>	repetitive peak reverse voltage			650			V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a>		30			A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; square-wave pulse		60			A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; <a href="#">Fig. 3</a>		250			A
		t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse		275			A
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 5</a>		-	1.85	2.50	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 5</a>		-	1.45	2.10	V
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	23	-	ns

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC31MY-650PS	IITO220-2L	BYC31MY-650PSQ	Tube	50	IITO220E-2L	03-Mar-2020

## 7. Marking

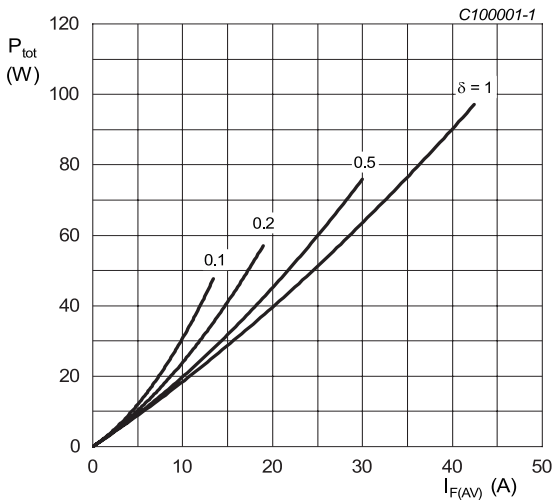
Table 4. Marking codes

Type number	Marking codes
BYC31MY-650PS	BYC31MY 650PS

8. Limiting values

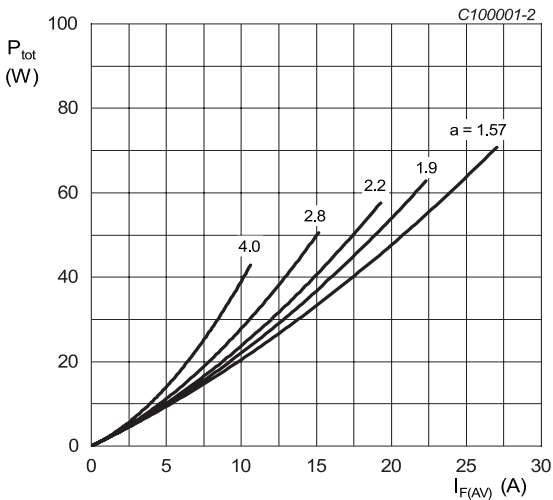
Table 5. Limiting values  
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{RWM}$	crest working reverse voltage			650	V
$V_R$	reverse voltage	DC		650	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a>		30	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25 \mu s$ ; square-wave pulse		60	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10 ms$ ; $T_{j(init)} = 25 \text{ }^\circ\text{C}$ ; sine-wave pulse; <a href="#">Fig. 3</a>		250	A
		$t_p = 8.3 ms$ ; $T_{j(init)} = 25 \text{ }^\circ\text{C}$ ; sine-wave pulse		275	A
$T_{stg}$	storage temperature			-65 to 175	$^\circ\text{C}$
$T_j$	junction temperature			-65 to 175	$^\circ\text{C}$



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   
 $V_o = 1.705 \text{ V}$ ;  $R_s = 0.0138 \text{ } \Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$   
 $V_o = 1.705 \text{ V}$ ;  $R_s = 0.0138 \text{ } \Omega$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

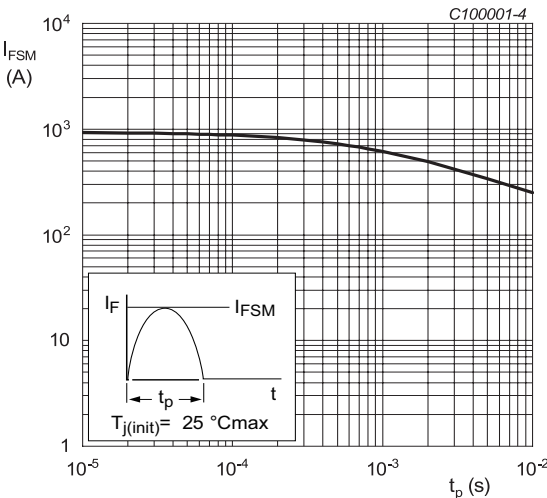


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 4</a>		-	-	2.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

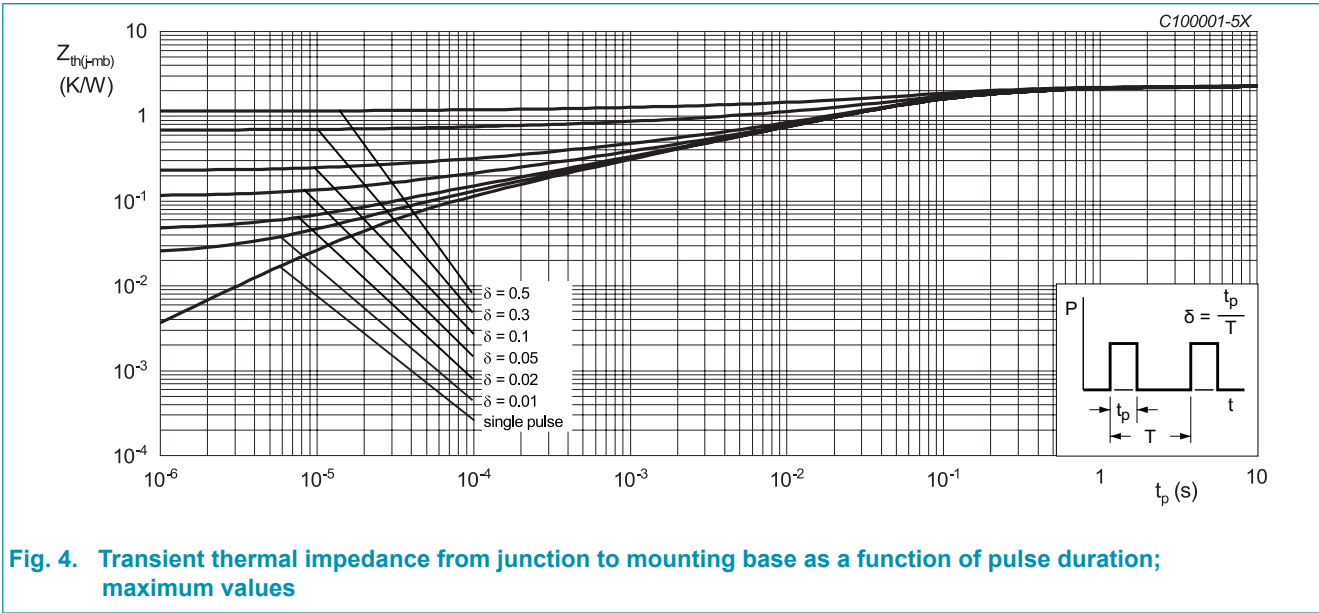


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

10. Isolation characteristics

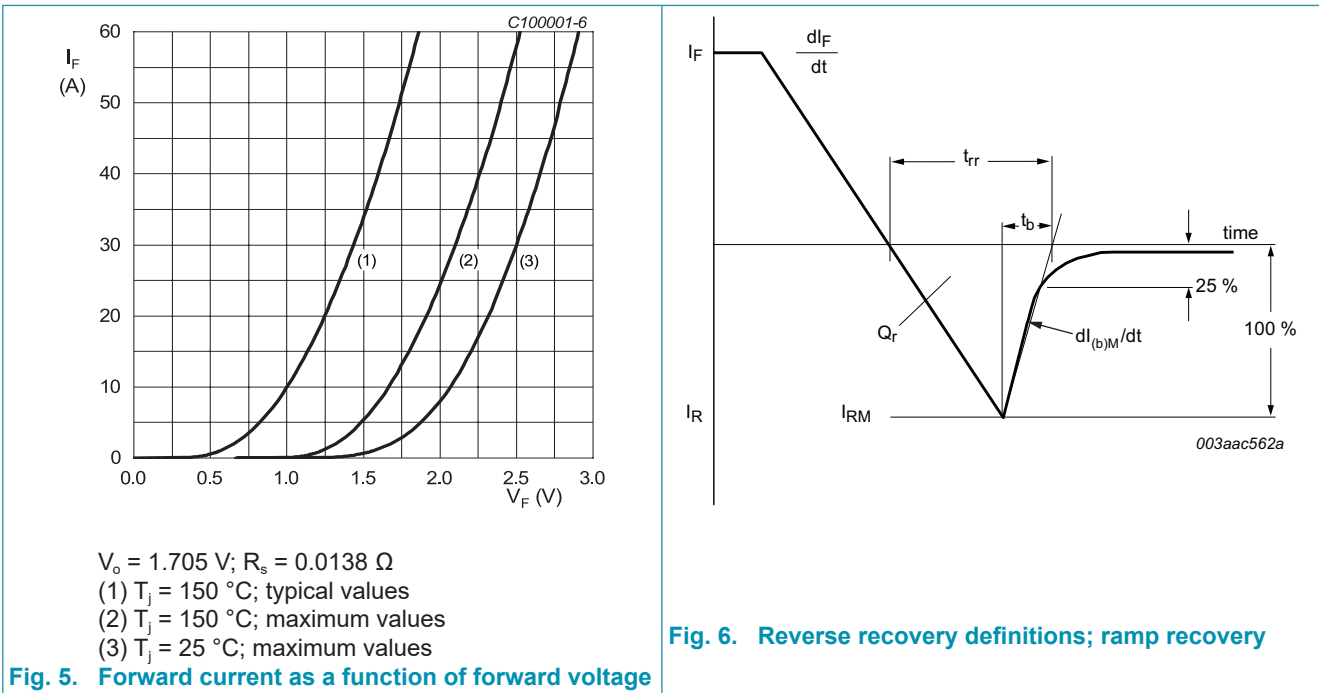
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
$C_{isol}$	isolation capacitance	f = 1 MHz; from cathode to external heatsink		-	10	-	pF

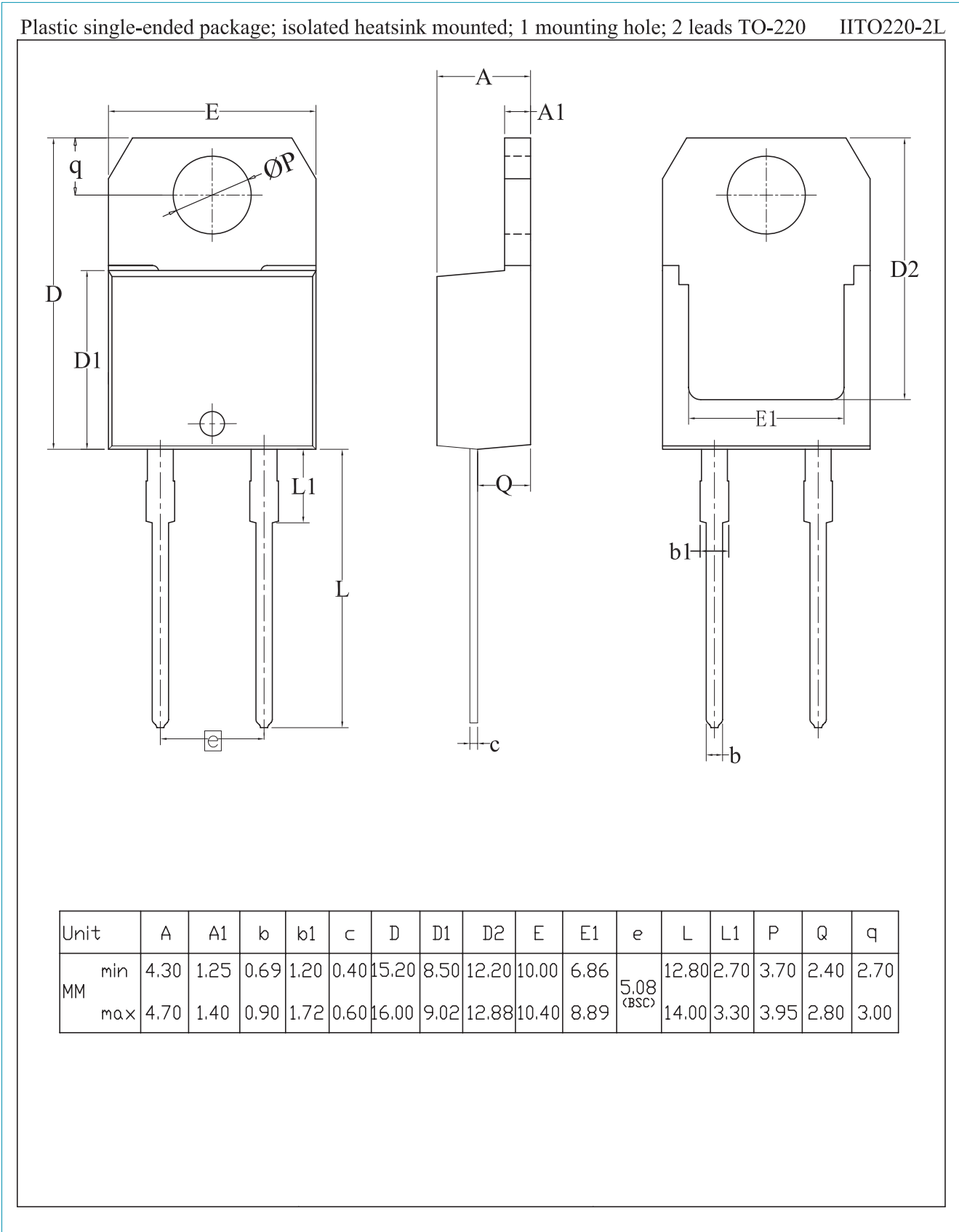
11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 5</a>		-	1.85	2.50	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 5</a>		-	1.45	2.10	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.2	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.05	-	mA
Dynamic characteristics							
Q <sub>r</sub>	reverse charge	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	200	-	nC
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 6</a>		-	650	-	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 0.5 A; I <sub>R</sub> = 1 A; I <sub>rr</sub> = 0.25 A; T <sub>j</sub> = 25 °C		-	36	-	ns
		I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	23	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	72	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 6</a>		-	121	-	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>		-	5.4	-	A
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 6</a>		-	10.8	-	A
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		16.8	-	-	mJ



12. Package outline



## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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